

Client Ref.:TSMC2002-1363

Our ref:0503-9856-US/Final/Vincent/Steve

#### **ABSTRACT OF THE DISCLOSURE**

5 A high voltage device comprising a substrate of a first type, a first and second well respectively of the first and a second type in the substrate, a gate formed on the substrate, a first and second doped region both of the second type, respectively formed in the first and second well and both sides of the gate, and a third doped region of the first type in the first well and adjacent to the first doped region.